

TOSHIBA**1SS391**

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS391

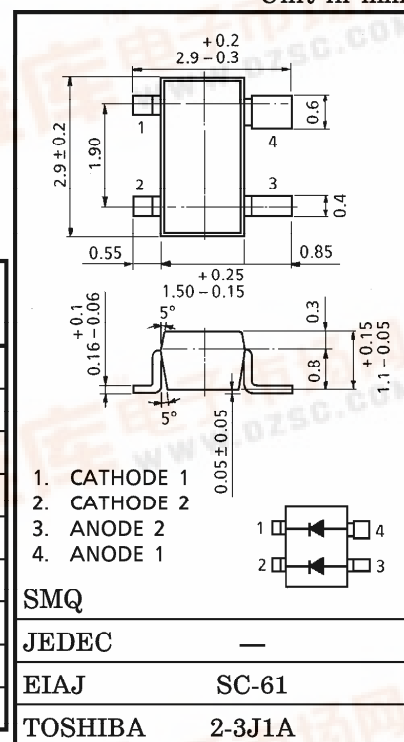
LOW VOLTAGE HIGH SPEED SWITCHING

Unit in mm

- Low Forward Voltage : $V_F(2) = 0.23V$ (Typ.) @ $I_F = 5mA$
- Small Package : SC-61

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Maximum (Peak) Forward Current	I_{FM}	200 ※	mA
Average Forward Current	I_O	100 ※	mA
Surge Current (10ms)	I_{FSM}	1 ※	A
Power Dissipation	P	150	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 125$	$^\circ C$
Operating Temperature Range	T_{opr}	$-40 \sim 100$	$^\circ C$



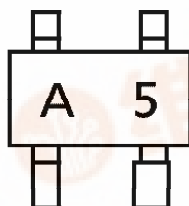
※ : Unit Rating. Total Rating=Unit Rating×1.5

Weight : 0.013g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F(1)$	$I_F = 1mA$	—	0.18	—	V
	$V_F(2)$	$I_F = 5mA$	—	0.23	0.30	V
	$V_F(3)$	$I_F = 100mA$	—	0.35	0.50	V
Reverse Current	I_R	$V_R = 10V$	—	—	20	μA
Total Capacitance	C_T	$V_R = 0, f = 1MHz$	—	20	40	pF

MARKING



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